

PATENT APPLICATION

Sheet 1 of 6

FORM PTO-1449 LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT (Use several sheets if necessary)	ATTY. DOCKET NO.	APPLICATION NO.	CONFIRMATION NO.
	200316545-1	10/799811	
	APPLICANT		
	Randy L. Hoffman, et al.		
	FILING DATE	GROUP	
	Herewith 3/12/2004	2815 - LANDAU	

REFERENCE DESIGNATION

U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	PUBLICATION DATE	NAME	Pages, Columns, Lines Where Relevant Passages or Figures Appear
<i>me</i>	1A	5744,864	08/28/1998	Cillessen, et al.	
<i>me</i>	1B	2003/0047785	03/13/2003	Kawasaki, et al.	
<i>me</i>	1C	2003/0111663	08/19/2003	Yagi	
<i>me</i>	1D	2003/0218221	11/27/2003	Wager, III, et al.	
<i>me</i>	1E	2003/0218222	11/27/2003	Wager, III, et al.	
<i>me</i>	1F	6,362,499	03/26/2002	Moise, et al.	
<i>me</i>	1G	6,391,462	05/21/2002	Jang	
<i>me</i>	1H	2002/171085	11/21/2002	Suzawa, et al.	
<i>me</i>	1I	60/490,239	07/25/2003		Transparent Thin Film Transistor with Zinc-Tin Oxide Channel...
<i>me</i>	1J	10/763,353	01/23/2004		Semiconductor Device
<i>me</i>	1K	10/763,354	01/23/2004		Trnasistor including a Deposited Channel Region Having a...

FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER	PUBLICATION DATE	NAME OF PATENTEE OR APPLICANT	Pages/Columns/Lines Where Relevant Passages/Figures Appear	Check if Translation attached
<i>me</i>	1L	WO 97/06544	02/20/1997	Cillessen, et al.		
<i>me</i>	1M	EP11134811	09/19/2001	Kawasaki, et al.		
	1N					
	1O					
	1P					

OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, etc.)

<i>me</i>	1Q	Aoki, Akira, et al., "Tin Oxide Thin Film Transistors", Japan J. Appl. Phys., Vol. 9, p.582 (1970).
<i>me</i>	1R	Carcia, P.F., et al., "Transparent ZnO thin-film transistor fabricated by rf magnetron sputtering", Applied Physics Letters, Vol. 82, No. 7, pp. 1117-1119 (February 17, 2003).
<i>me</i>	1S	Carcia, P.F., et al., "ZnO Thin Film Transistors for Flexible Electronics", Mat. Res. Soc. Symp. Proc., Vol. 769, pp. H72.1-H72.6 (2003).

EXAMINER

DATE CONSIDERED

*Michael C. Jensen**4/12/06*

PATENT APPLICATION

Sheet 2 of 6

FORM PTO-1449 LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT (Use several sheets if necessary)	ATTY. DOCKET NO. 200316545-1	APPLICATION NO. 10/799811	CONFIRMATION NO.
	APPLICANT Randy L. Hoffman, et al.		
	FILING DATE Herewith 3/12/2004	GROUP 2815 London	

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EXAMINER INITIAL		DOCUMENT NUMBER	PUBLICATION DATE	NAME	Pages, Columns, Lines Where Relevant Passages or Figures Appear
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	2L					
	2M					
	2N					
	2O					
	2P					

OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, etc.)

m	2Q	Fu, Shelton, et al., "MOS and MOSFET with Transistion Metal Oxides", SPIE Vol. 2697, pp. 520-527. 1996
m	2R	Giesbers, J.B., et al., "Dry Etching of All-Oxide Transparent Thin Film Memory Transistors", Microelectronic Engineering, Vol. 35, pp. 71-74 (1997).
m	2S	Grosse-Holz, K.O., et al. "Semiconductive Behavior of Sb Doped SnO2 Thin Films", Mat. Res. Soc. Symp. Proc., Vol. 401, pp. 67-72 (1996).

EXAMINER

Michael C. [Signature]

DATE CONSIDERED

4/12/06

PATENT APPLICATION

Sheet 3 of 6

FORM PTO-1449 LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT (Use several sheets if necessary)	ATTY. DOCKET NO. 200316545-1	APPLICATION NO. 10799874	CONFIRMATION NO.
	APPLICANT Randy L. Hoffman, et al.		
	FILING DATE Herewith 3/12/2004	GROUP 2815 London	

REFERENCE DESIGNATION

U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	PUBLICATION DATE	NAME	Pages, Columns, Lines Where Relevant Passages or Figures Appear
	3A			
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	3L				
	3M				
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	3P				

OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, etc.)

m	3Q	Hoffman, R.L., et al., "ZnO-based transparent thin-film transistors", Applied Physics Letters, Vol. 82, No. 5, pp. 733-735 (February 3, 2003).
m	3R	Masuda, Satoshi, et al., "Transparent thin film transistors using ZnO as an active channel layer and their electrical properties", Journal of Applied Physics, Vol. 93, No. 3, pp. 1624-1630 (February 1, 2003).
m	3S	Nishi, Junya, et al., "High Mobility Thin Film Transistors with Transparent ZnO Channels", Jpn. J. Appl. Phys., Vol. 42, Part 2, No. 4A, pp. L347-L349 (April, 2003).

EXAMINER

DATE CONSIDERED

PATENT APPLICATION

Sheet 4 of 6

FORM PTO-1449

LIST OF PATENTS AND PUBLICATIONS FOR
APPLICANT'S INFORMATION DISCLOSURE
STATEMENT

(Use several sheets if necessary)

ATTY. DOCKET NO.

200316545-1

APPLICATION NO.

10/799811

CONFIRMATION NO.

APPLICANT

Randy L. Hoffman, et al.

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U.S. PATENT DOCUMENTS

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4L				
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OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, etc.)

4Q	Ohya, Yutaka, et al., "Thin Film Transistor of ZnO Fabricated by Chemical Solution Deposition", Jpn. J. Appl. Phys., Vol. 40, Part 1, No. 1, pp. 297-298 (January, 2001).
4R	Pallecchi, Ilaria, et al. "SrTiO3-based metal-insulator-semiconductor heterostructures" Applied Physics Letters, Vol. 78, No. 15, pp. 2244-2246 (April 9, 2001).
4S	Prins, M. W. J., et al., "A ferroelectric transparent thin-film transistor", Appl. Phys. Lett., Vol. 68, No. 25, pp. 3650-3652 (June 17, 1996).

EXAMINER

Matthew C. Janbur

DATE CONSIDERED

4/12/06

PATENT APPLICATION

Sheet 5 of 6

FORM PTO-1449

LIST OF PATENTS AND PUBLICATIONS FOR
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(Use several sheets if necessary)

ATTY. DOCKET NO.

200316545-1

APPLICATION NO.

10/799811

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APPLICANT

Randy L. Hoffman, et al.

FILING DATE

Herewith 3/14/2004

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2815 London

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U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	PUBLICATION DATE	NAME	Pages, Columns, Lines Where Relevant Passages or Figures Appear
	5A				
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	5L					
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m	5Q	Seager, C.H., et al., "Charge Trapping and device behavior in ferroelectric memories", Appl. Phys. Lett., Vol. 68, No. 19, pp. 2660-2662 (May 6, 1996).
m	5R	Uneno, K., et al. "Field-effect transistor on SrTiO3 with sputtered Al2O3 gate insulator", Applied Physics Letters, Vol. 83, No. 9, pp. 1755-1757 (September 1, 2003).
m	5S	Wöllenstein, Jürgen, et al., "An Insulated gate thin-film transistor using SnO2 as semiconducting channel, a possible new gas sensor device" The 11th European Conference on Solid State Transducers, pp. 471-474 (September 21-24, 1997).

EXAMINER

Michael C. Johnson

DATE CONSIDERED

4/12/06

PATENT APPLICATION

Sheet 6 of 6

FORM PTO-1449

LIST OF PATENTS AND PUBLICATIONS FOR
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ATTY. DOCKET NO.

200316545-1

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APPLICANT

Randy L. Hoffman, et al.

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Herewith 3/12/2004

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U.S. PATENT DOCUMENTS

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	6N				
	6O				
	6P				

OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, etc.)

m	6Q	Yoshida, A., "Three Terminal Field Effect Superconducting Device Using SrTiO ₃ Channel" IEEE Transactions on Applied Superconductivity, Vol. 5, No. 2, pp. 2892-2895 (June, 1995).
m	6R	Solid-State Electronics, Vol. 7, Pergamon Press, Notes pp. 701-702 (1964).
m	6S	Anonymous, "Transparent and/or memory thin film transistors in LCD's and PLEAD," Research Disclosure, p. 890 (July 1998).

EXAMINER

Michael C. Fisher

DATE CONSIDERED

4/17/06

Class 3
Sub Class